

**INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION**

(PTO-1449)

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64965-168SERIAL NO.
*Divisional of Application
10/015,808
10/620,605*APPLICANT
QI XIANGFILING DATE
July 17, 2003GROUP
To be assigned**US PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>SWC</i>		US 20020123167A1	09/2002	Fitzgerald	
		US 6,407,406 B1	7/2002	Tezuka	
		US 6,214,653 B1	04/2001	Chen et al	
		US 6,313,486 B1	11/2001	Kencke et al	
		US 0,008,284 A1	7/2001	Huang	
		US 6,251,751 B1	6/2001	Chu et al	
		US 0,003,269 A1	6/2001	Wu et al	
		US 5,759,898	6/1998	Ek et al	
		US 0,024,884 A1	9/2001	Fitzgerald	
		US 6,039,803	3/2000	Fitzgerald et al	
		US 0,016,383 A1	8/2001	Chen et al	
		US 6,180,490 B1	1/2001	Vassilev et al	
		US 6,300,172 B1	10/2001	Ang et al	
<i>SWC</i>		US 6,207,530 B1	3/2001	Hsu et al	
		US			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
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OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
<i>SWC</i>		Shallow Trench Isolation, "Trench Isolation," http://courses.nus.edu.sg/course/phy/ >pgs. 1-4	
		Hitachi America, Ltd., Semiconductor Equipment Group, "Customizable Shallow Trench Isolation, http://www.hitachi.com/semiequipment/sti.html > pg 1	
		SNP Applications/Shallow Trench Isolation (STI), "Shallow Trench Isolation (STD)," http://www.surfaceinterface.com/snappssti.html >, pgs 1-2	
<i>SWC</i>		Institute of Microelectronics - Deep Submicron - Shallow Trench Isolation, "Shallow Trench Isolation Module Developmetn", http://www.ime.org.sg/deep_trench.htm >, pgs. 1-2	

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DATE CONSIDERED

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FOREIGN/PATENT DOCUMENTS						
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SWL		David Lammers, "MIT spinout preps commercial strained silicon", Oct. 22, 2001, http://www.eetimes.com/story/OEG20011022S0078/ , pgs. 1-5				
		IBM's Strained Silicon Breakthrough Image Page, June 8, 2001, http://www.research.ibm.com/resources/press/strainsilicon/ , pgs. 1-2				
		Dennis Sellers, "It isn't just IBM that has 'strained silicon' technology", June 14, 2001, http://maccentral.macworld.com/news/0106/14.silicon.shtml , pgs. 1-5				
		Matthew French, "Amber Wave Systems 'strained silicon' significant for semiconductor industry", August 6, 2001, http://www.mass.../displaydetail.asp? , pgs. 1-3				
		Richard Ball, "Strained silicon wafers boost FET speed 80 per cent at US start-up", Electronics Weekly Archive, pg. 1				
		Orla Higgins, Press Release, "Amber Wave Systems Corporation Announces Availability of Breakthrough Strained Silicon Technology", October 22, 2001, pgs. 1-4				
SWL		Mark A. Wolf, Pres Release, Amberwave Announces Strained Silicon Technology Available Immediately, June 8, 2001, pg. 1				
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